

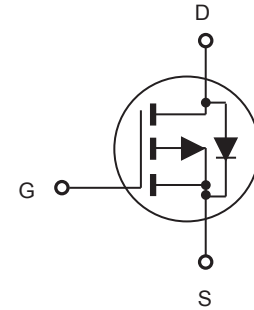


# CEP35P10/CEB35P10 CEF35P10

## P-Channel Enhancement Mode Field Effect Transistor

### FEATURES

- -100V, -32A,  $R_{DS(ON)} = 76m\Omega$  @  $V_{GS} = -10V$ .  
 $R_{DS(ON)} = 92m\Omega$  @  $V_{GS} = -4.5V$ .
- Super high dense cell design for extremely low  $R_{DS(ON)}$ .
- High power and current handling capability.
- Lead-free plating ; RoHS compliant.
- TO-220 & TO-263 package.



### ABSOLUTE MAXIMUM RATINGS $T_C = 25^\circ C$ unless otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	$V_{DS}$	-100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	-32	A
Drain Current-Pulsed <sup>a</sup>	$I_{DM}$	-128	A
Maximum Power Dissipation @ $T_C = 25^\circ C$	$P_D$	125	W
- Derate above $25^\circ C$		0.83	W/ $^\circ C$
Single Pulsed Avalanche Energy <sup>e</sup>	$E_{AS}$	450	mJ
Single Pulsed Avalanche Current <sup>e</sup>	$I_{AS}$	30	A
Operating and Store Temperature Range	$T_J, T_{stg}$	-55 to 175	$^\circ C$

### Thermal Characteristics

Parameter	Symbol	Limit	Units
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.2	$^\circ C/W$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	$^\circ C/W$



# CEP35P10/CEB35P10 CEF35P10

## Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-100			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -100V, V_{GS} = 0V$			-1	$\mu A$
Gate Body Leakage Current, Forward	$I_{GSSF}$	$V_{GS} = 20V, V_{DS} = 0V$			100	nA
Gate Body Leakage Current, Reverse	$I_{GSSR}$	$V_{GS} = -20V, V_{DS} = 0V$			-100	nA
<b>On Characteristics <sup>c</sup></b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}, I_D = -250\mu A$	-1		-3	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -16A$		63	76	$m\Omega$
		$V_{GS} = -4.5V, I_D = -8A$		72	92	$m\Omega$
<b>Dynamic Characteristics <sup>d</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = -25V, V_{GS} = 0V,$ $f = 1.0\text{ MHz}$		2590		pF
Output Capacitance	$C_{oss}$			320		pF
Reverse Transfer Capacitance	$C_{rss}$			45		pF
<b>Switching Characteristics <sup>d</sup></b>						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -50V, I_D = -18A,$ $V_{GS} = -10V, R_{GEN} = 3.3\Omega$		17		ns
Turn-On Rise Time	$t_r$			6		ns
Turn-Off Delay Time	$t_{d(off)}$			75		ns
Turn-Off Fall Time	$t_f$			10		ns
Total Gate Charge	$Q_g$	$V_{DS} = -80V, I_D = -18A,$ $V_{GS} = -10V$		75		nC
Gate-Source Charge	$Q_{gs}$			9		nC
Gate-Drain Charge	$Q_{gd}$			18		nC
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
Drain-Source Diode Forward Current <sup>b</sup>	$I_S$				-32	A
Drain-Source Diode Forward Voltage <sup>c</sup>	$V_{SD}$	$V_{GS} = 0V, I_S = -16A$			-1.2	V
<b>Notes :</b> □ a.Repetitive Rating : Pulse width limited by maximum junction temperature. □ b.Surface Mounted on FR4 Board, $t \leq 10\text{ sec.}$ □ c.Pulse Test : Pulse Width $\leq 300\mu s,$ Duty Cycle $\leq 2\%.$ □ d.Guaranteed by design, not subject to production testing. □ e.L = 1mH, $I_{AS} = 30A,$ $V_{DD} = 25V,$ $R_G = 25\Omega,$ Starting $T_J = 25\text{ C.}$ □						



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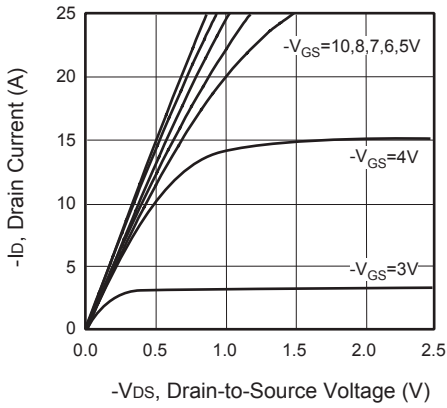


Figure 1. Output Characteristics

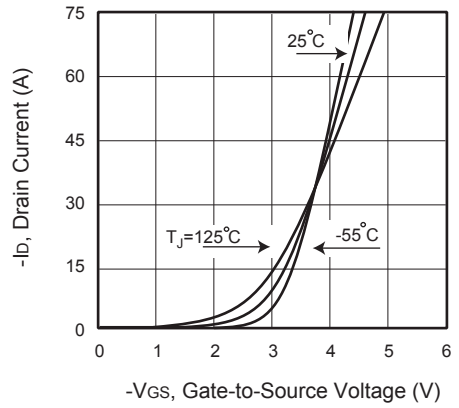


Figure 2. Transfer Characteristics

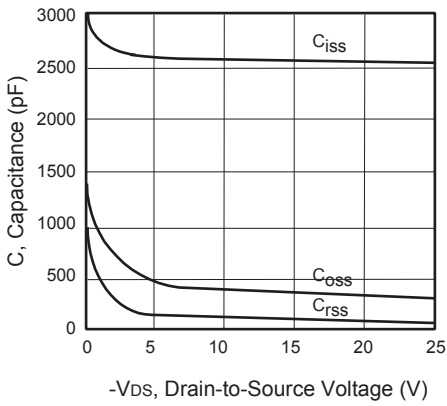


Figure 3. Capacitance

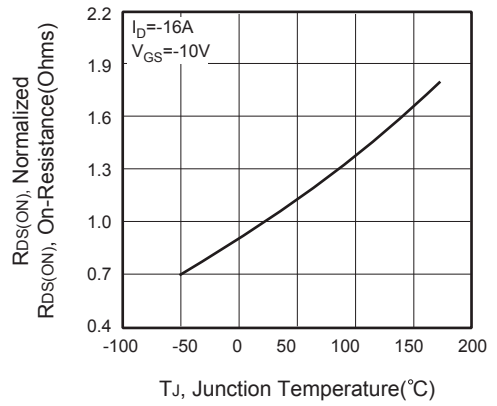


Figure 4. On-Resistance Variation with Temperature

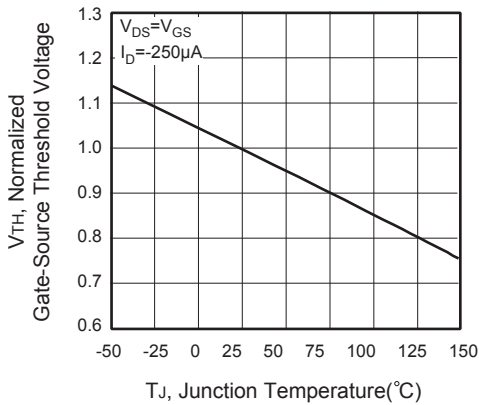


Figure 5. Gate Threshold Variation with Temperature

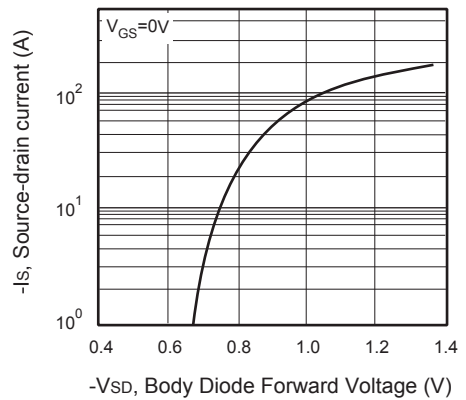


Figure 6. Body Diode Forward Voltage Variation with Source Current

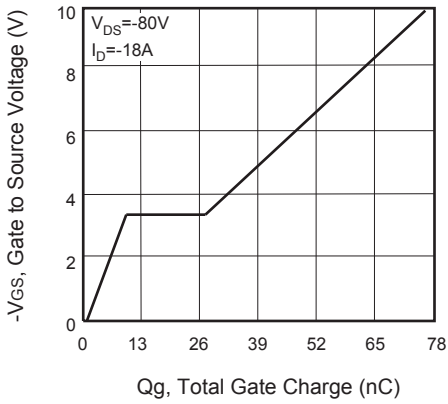


Figure 7. Gate Charge

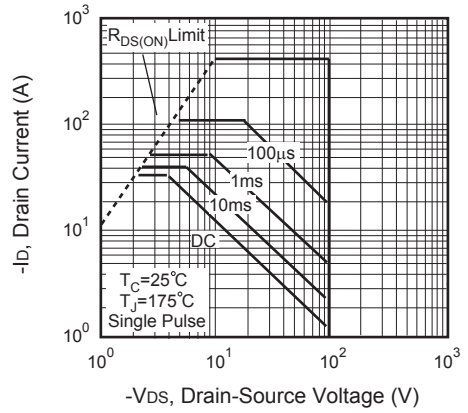


Figure 8. Maximum Safe Operating Area

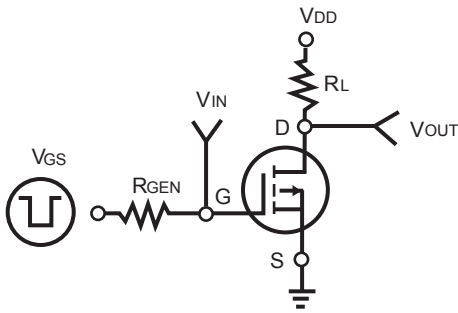


Figure 9. Switching Test Circuit

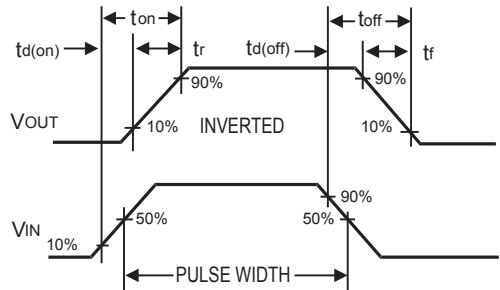


Figure 10. Switching Waveforms

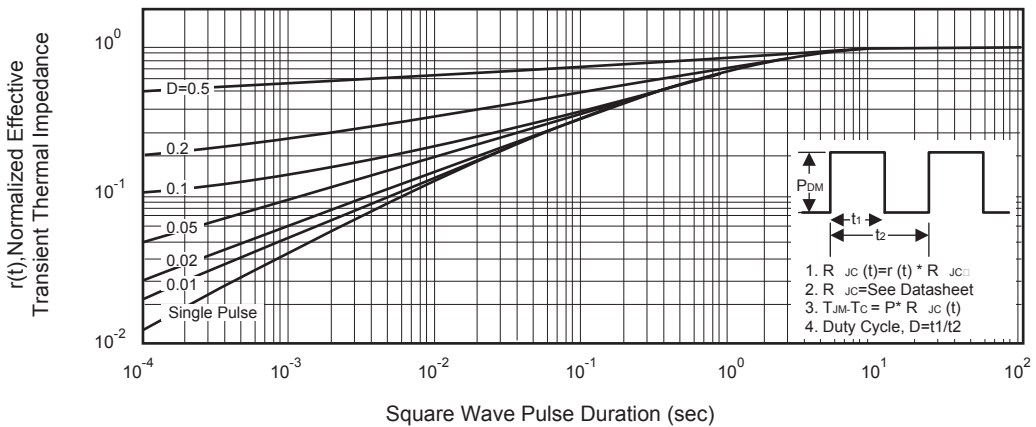


Figure 11. Normalized Thermal Transient Impedance Curve